

Synchrotron EXAFS & XANES techniques for Chemical Speciation on Environmental Systems

ALBA, 6/10/2014 - 9/10/2014



Laura Simonelli

CLÆSS (Core Level Absorption & Emission Spectroscopies) beamline responsible



OUTLINE





- The multiple scattering region (XANES)
- The single scattering region (EXAFS)
- Detection methods
- Research field
- Summary



X-rays

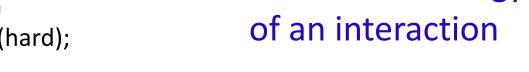


X-ray Absorption Spectroscopy (XAS)

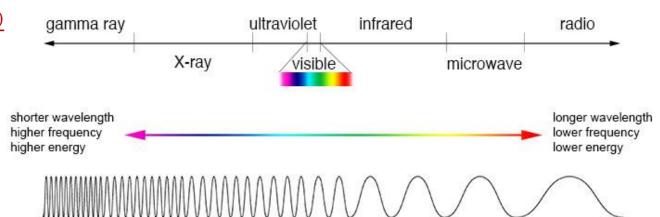
probe

electromagnetic radiation E from 120 eV (soft) to 120 keV (hard); λ from 100 Å to 0.1 Å

$$E(keV) = \frac{12.4 (keV)}{\lambda (\text{Å})}$$



measure the energy



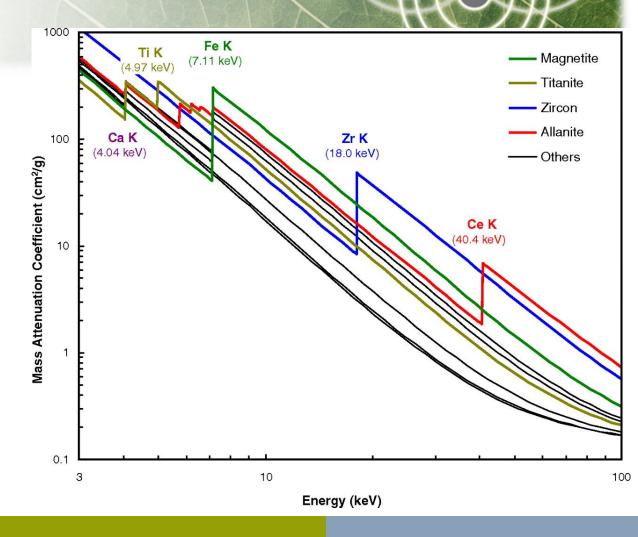




The oscillating electric field of the electromagnetic radiation interacts with the electrons bound in an atom.

Scattered radiation

Absorbed radiation



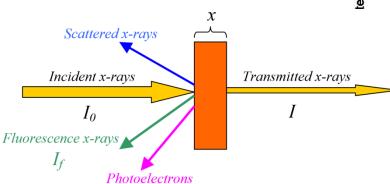


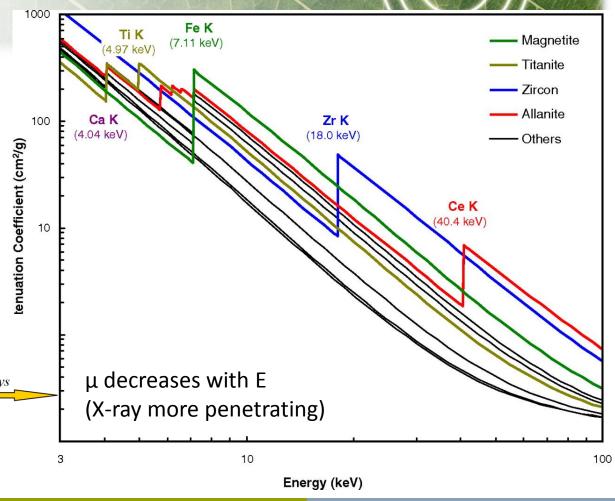


A monochromatic x-ray beam of intensity I_0 passing through a sample of thickness x will get a reduced intensity I according to:

In
$$(I_0/I) = \mu x$$

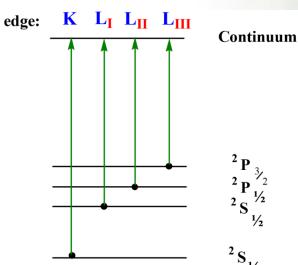
 μ = linear absorption coefficient





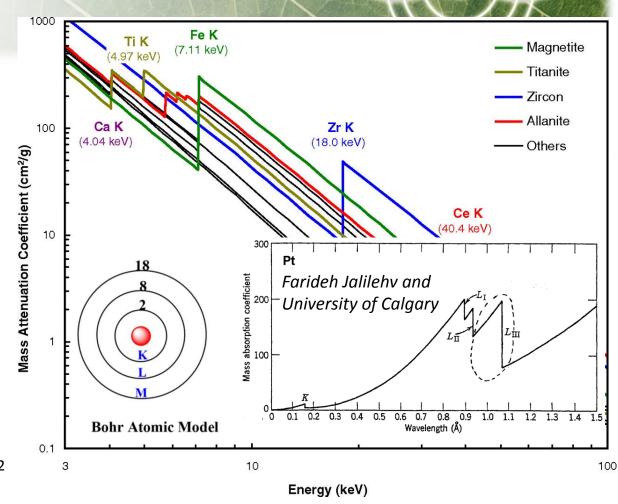






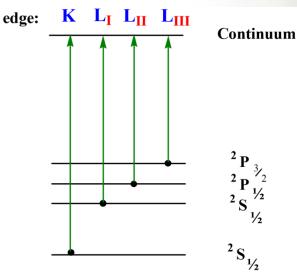
Absorption edges occur for each shell of core electrons when E = binding energy of core electron

K: $1s_{1/2}$ **L**₁: $2s_{1/2}$ **L**₂: $2p_{1/2}$ **L**₃: $2p_{3/2}$ (n l_i notation)



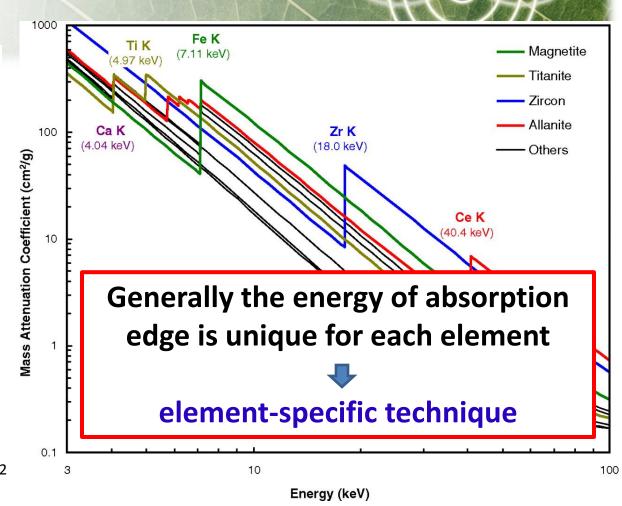






Absorption edges occur for each shell of core electrons when E = binding energy of core electron

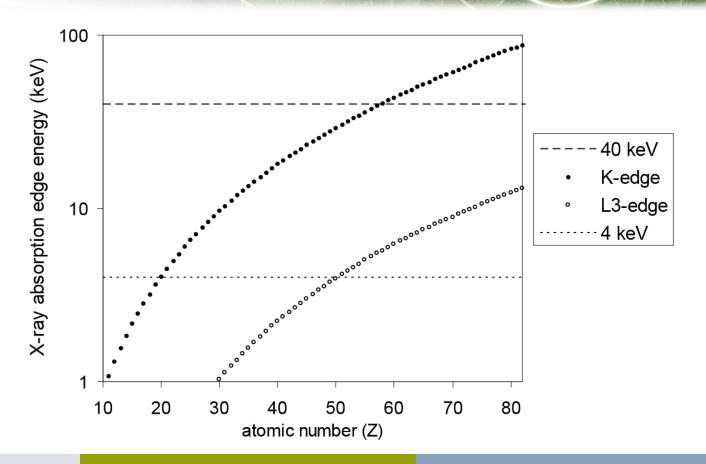
K: $1s_{1/2}$ **L**₁: $2s_{1/2}$ **L**₂: $2p_{1/2}$ **L**₃: $2p_{3/2}$ (n l_i notation)





difficult for light elements, e.g. Z<22 (Ti) for heavy elements use L3 edge, e.g. Z>57 (La)







Photoelectron like a wave

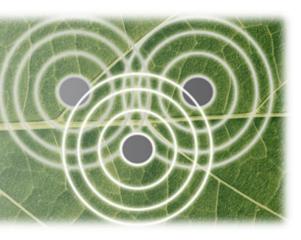
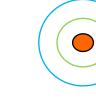


photo-electron excited to state significantly above binding energy – becomes "quasi" free-electron

Atomic absorption





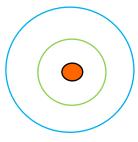
The photo-electron leaves the excited atom with circular wavefunction – wavelength $\lambda = \frac{12.2}{\sqrt{KE(eV)}}$ (kinetic energy KE = E - binding energy)



higher E, larger KE, Smaller λ

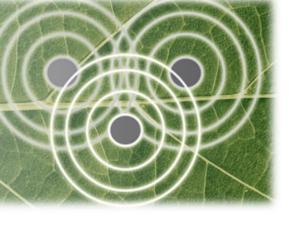


lower E, smaller KE, larger λ

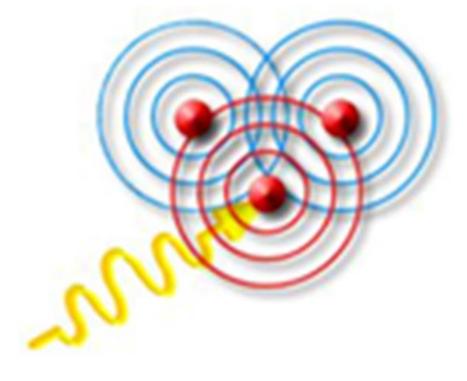




Photon absorption: Photoelectron like a wave



When the photoelectron leaves the absorbing atom, its wave is backscattered by the neighboring atoms.

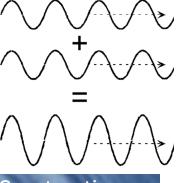




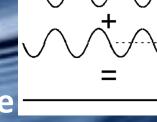
Interference of scattered waves



Interference is essentially an energy redistribution process: the energy which is lost at the destructive is regained at the constructive interference.



Constructive



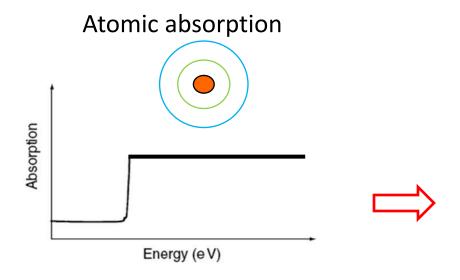
destructive

Constructive and destructive interference between the outgoing photoelectron wave and backscattered wave



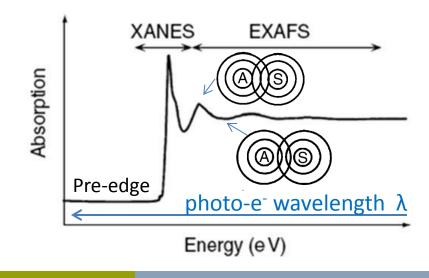
Absorber isolated or embedded in the matter





The absorption of an isolated atom show a step like behavior.

When the absorber is embedded in the matter the photoexcitation cross-section is modulated by the interference between the outgoing and the back-scattered photoelectron waves.





Photon absorption: XANES & EXAFS

XANES (or NEXAFS)

(X-ray Absorption Near Edge Structure):

$$\approx$$
 -10 eV < E-E₀ < 50 eV

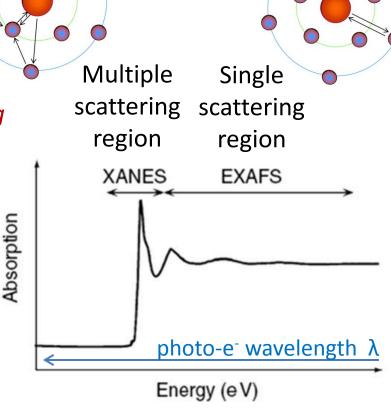
Lower energy \implies Higher $\lambda \implies$ multiple scattering

EXAFS

(Extended X-ray Absorption Fine Structure):

$$\approx$$
 50 eV < E-E₀ < 1000 eV

Higher energy \longrightarrow Lower $\lambda \longrightarrow$ single scattering





Photon absorption: XANES

XANES (or **NEXAFS**)

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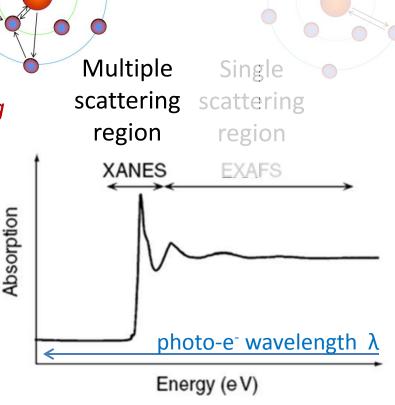
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structural and electronic properties

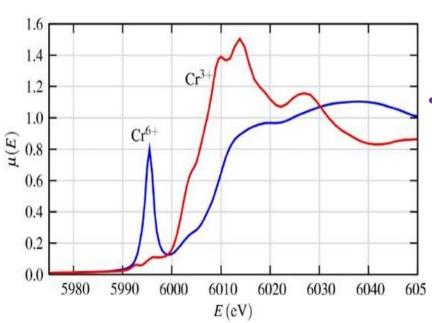


ELECTRONIC AND STRUCTURAL PROPERTIES

Energy, width, and intensity



- Oxidation state
- Unoccupied electronic states
 - Spin state
 - Local structure



Angle dependence of multiple scattering



direct information about bond angles.



structural and electronic properties

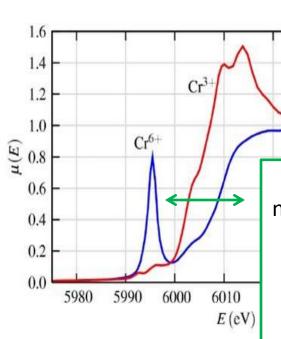


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Angle dependence of multiple scattering



direct information about bond angles.

The energy of an absorption edge is not well defined. It can be taken as the energy at half-height or as the maximum in the first derivative with respect to energy. It shifts as a function of the oxidation state

Laura Simonelli

XAS (XANES/EXAFS)

6/10/2014



structural and electronic properties

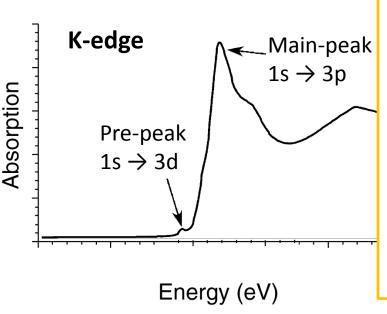


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The most intense features are due to electric-dipole allowed transitions (i.e. $\Delta \ell$ = \pm 1) to unoccupied final states. The most intense features of a K-edge are due to transitions from 1s \rightarrow p-like final states, while the most intense features of the L₃-edge are due to 2p \rightarrow d-like final states.



structural and electronic properties

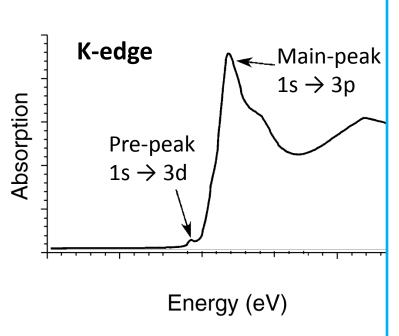


ELECTRONIC AND STRUCTURAL PROPERTIES

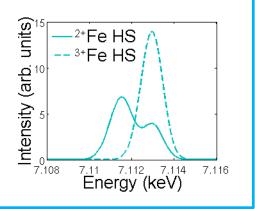
Energy, width, and intensity



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Theoretical simulation of the pre-edge region for tetrahedral high-spin ²⁺Fe (solid line) and ³⁺Fe (dashed line) complexes





structural and electronic properties



Angle dependence of multiple scattering



direct information about bond angles.

XANES often used as simple "fingerprint" to identify presence of a particular chemical species.

ELECTRONIC AND STRUCTURAL PROPERTIES

Energy, width, and intensity

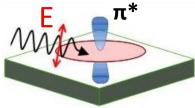


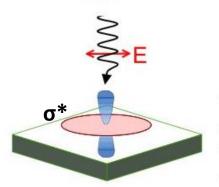
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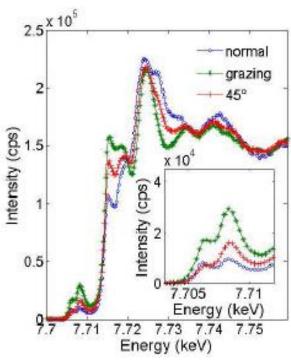


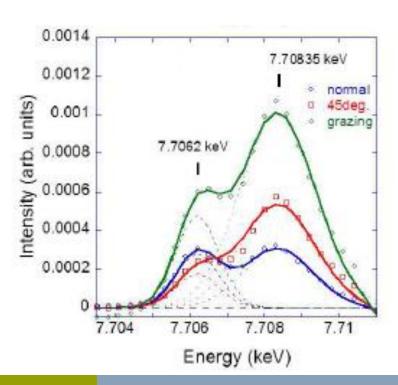






The chosen angle of incidence favors either excitations into the π^* (top) or the σ^* (bottom) orbitals.



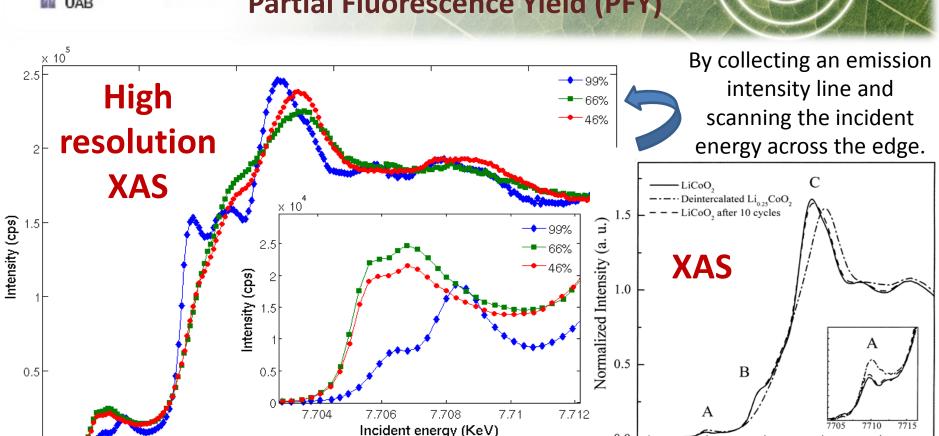




Grup de Tècniques de Separació en Química

XANES:

High resolution x-ray absorption or Partial Fluorescence Yield (PFY)



7.72

7.73

Incident energy (KeV)

7.74

7.75

Energy /eV

7730

7740

7720

7700

7710



Photon absorption: **EXAFS**

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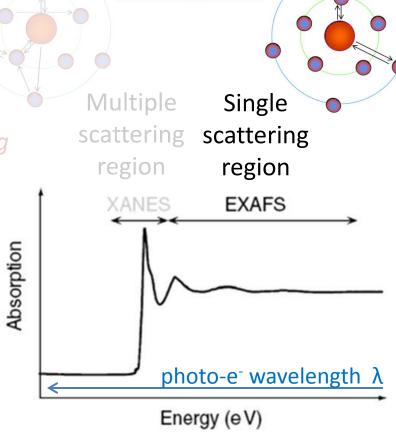
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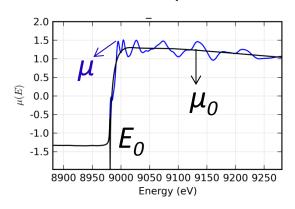


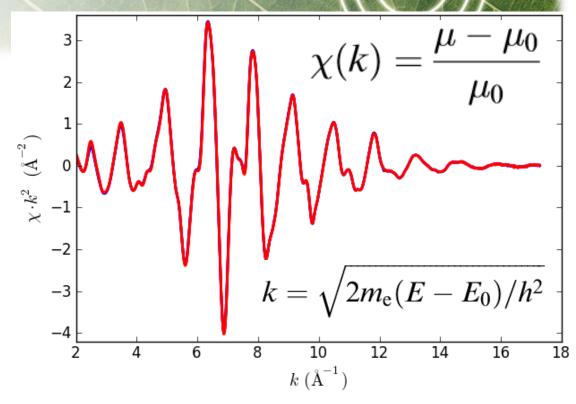


The $\chi(k)$ function



The structural information are encoded in the amplitude, shape, phase, and frequency of the oscillations represented by χ.





For a single absorber–scatterer pair the interferences will give rise to sinusoidal oscillations in μ if the energy is given in units proportional to the photoelectron wavevector, k, and the threshold energy, E_0 , is the binding energy of the photoelectron.



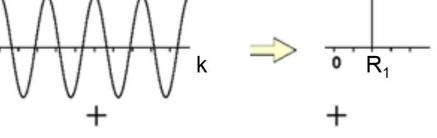
de Separació en Química UAB

EXAFS:

The Fourier transform of sin(2kR)



Interference gives an oscillating function of wavevector k

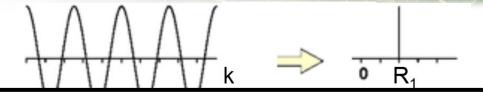


 $k \Rightarrow R_1 R_2$

Fourier Transform
Gives a peaked
function of
distance R

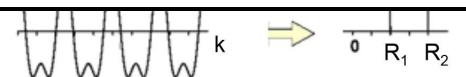


The Fourier transform



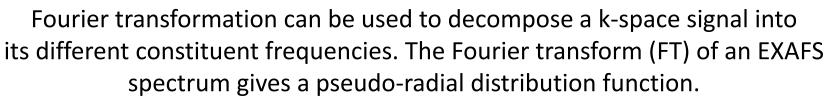
Interfere an os fun of wave A good Fourier Transform requires large value of k, hence large range of E

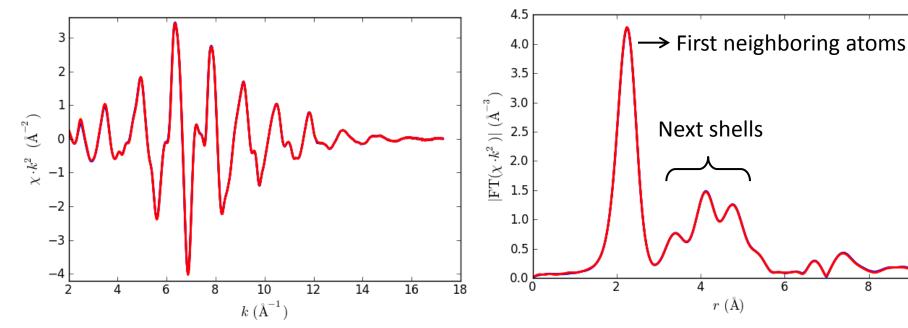
scan X-ray energy up to $E_0+1000 \text{ eV}$ photo-electron k up to 16 Å⁻¹ ransform peaked ion of nce R





The Fourier transform



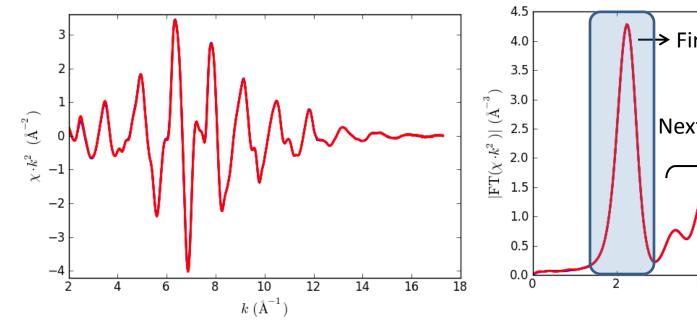


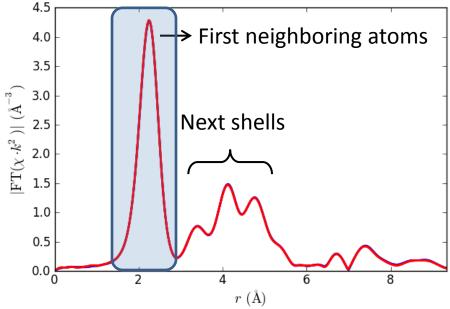


Filtered back Fourier analysis



First shell parameters can be obtained by fitting directly the filtered back Fourier transform.



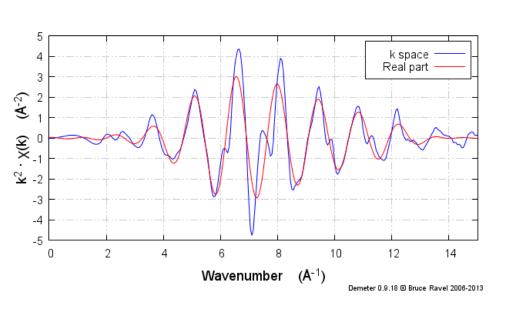


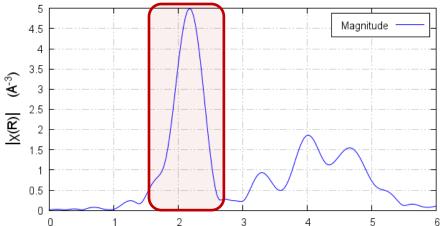


Filtered back Fourier analysis



First shell parameters can be obtained by fitting directly the filtered back Fourier transform.





Radial distance

First neighboring atoms

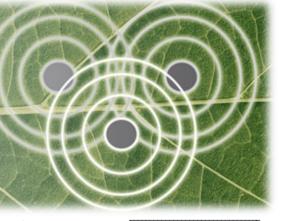
Demeter 0.9.18 @ Bruce Ravel 2006-2013



Grup de Tècniques de Separació en Quimica

EXAFS:

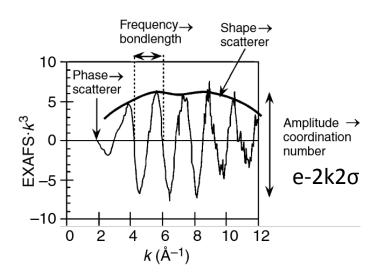
The $\chi(k)$ function modeling



$$\chi(k) = \frac{\mu - \mu_0}{\mu_0}$$
 $k = \sqrt{2m_{\rm e}(E - E_0)/h^2}$

$$\chi(k) = \sum_{i} \frac{N_{i} S_{0}^{2}}{kR_{i}^{2}} f_{i}(k, R_{i}) e^{-\frac{2R_{i}}{\lambda}} e^{-2k^{2} \sigma_{i}^{2}} \sin[2kR_{i} + \delta_{i}(k)]$$

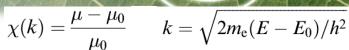
The amplitude of the oscillations is proportional to the number of scattering atoms N_i , the frequency of the oscillations is inversely proportional to the absorber-scatterer distance R_i , and the shape of the oscillations is determined by the energy dependence of the photoelectron scattering, which depends on the identity of the scattering atom.







The $\chi(k)$ function modeling



$$\chi(k) = \sum_{i} \frac{N_{i} S_{0}^{2}}{kR_{i}^{2}} f_{i}(k, R_{i}) e^{-\frac{2R_{i}}{\lambda}} e^{-2k^{2}\sigma_{i}^{2}} \sin[2kR_{i} + \delta_{i}(k)]$$

 $N_i = 3 \cos^2 \vartheta_i$ mumber of neighboring atoms at a distance R_i at an angle ϑ_i with respect to the x-ray beam polarization.

 S_0^2 passive electrons reduction factor (to allow for inelastic loss processes)

 $f_i(k, R_i)$ backscattering amplitude (energy dependence of the photoelectron scattering)

 λ photoelectron mean free path

 δ_i phase shift (that the photoelectron wave undergoes when passing through the potential of the absorbing and scattering atoms)

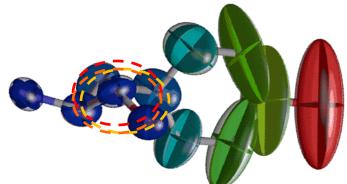
 σ_i^2 correlated Debye–Waller factor (root-mean-square deviation in absorber–scatterer distance)





Static and dynamic disorder
Temperature dependence of the DW

$$\chi(k) = \sum_{i} \frac{N_{i} S_{0}^{2}}{kR_{i}^{2}} f_{i}(k, R_{i}) e^{-\frac{2R_{i}}{\lambda}} e^{-2l^{2}\sigma_{i}^{2}} \sin[2kR_{i} + \delta_{i}(k)]$$



$$\sigma^2 = \sigma_0^2 + \sigma^2(T)$$

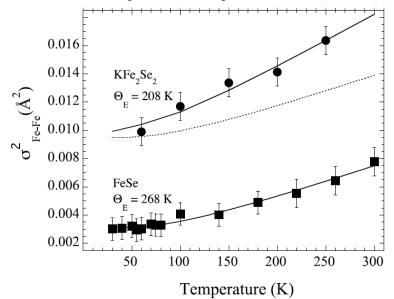
$$\sigma^2(T) = \frac{\hbar^2}{2\mu k_{\rm B}\theta_{\rm E}} \coth\frac{\theta_{\rm E}}{2T}$$





Static and dynamic disorder
Temperature dependence of the DW

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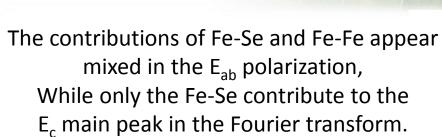
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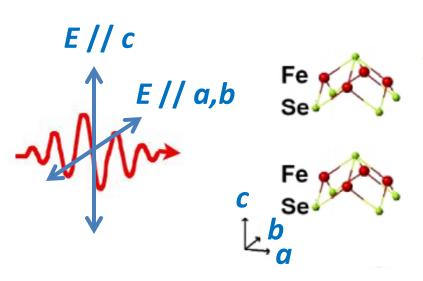
Einstein's formula:

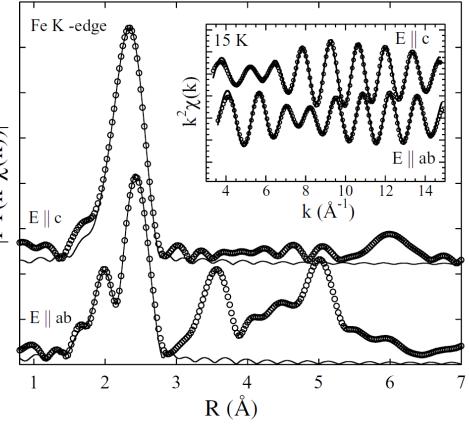
$$\sigma^2(T) = \frac{\hbar^2}{2\mu k_{\rm B}\theta_{\rm E}} \coth\frac{\theta_{\rm E}}{2T}$$



Polarization analysis



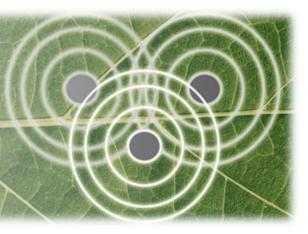






EXAFS & XANES:

Complementary information



XANES

- Oxidation state
- Unoccupied electronic states
 - Spin state
 - Local structure
- direct information about bond angles.

EXAFS

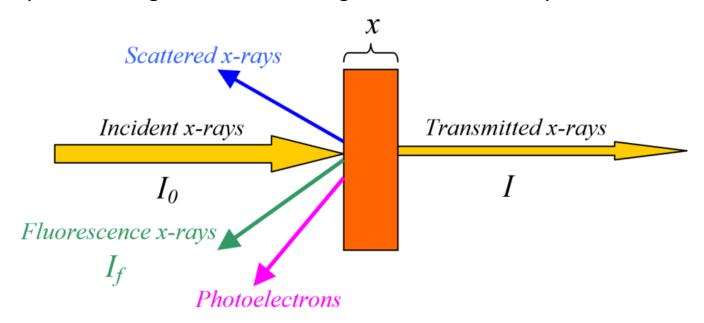
- Bond distances
- Coordination number
- Static and dynamic disorder



Detection methods:

Transmission & fluorescence modes

Absorption of an ionizing X-ray results in photoelectron ejection, leaving behind a highly excited core-hole state. This can relax by a variety of mechanisms, with the two most important being emission of an Auger electron and X-ray fluorescence.



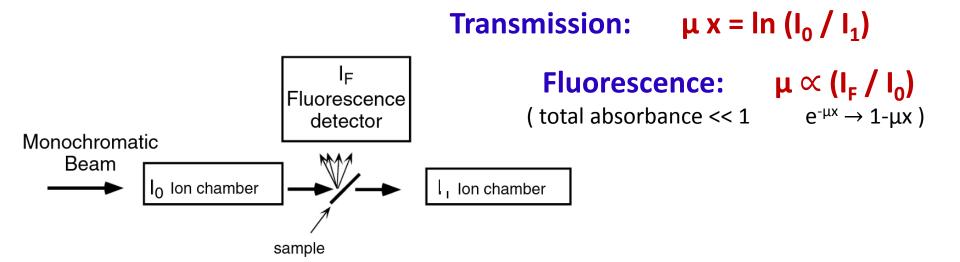


Detection methods:

Transmission & fluorescence modes

Providing the sample is dilute or thin (total absorbance <<1), the intensity of the fluorescence X-rays is proportional to the X-ray absorption cross-section.

In order to have good sensitivity, the fluorescence detector needs some kind of energy resolution to distinguish between the signal and background X-rays.





Fluorescence method and the self absorption effect



FLUORESCENCE MODE:

 $\mu \propto (I_F / I_0)$ is only true in the limit of very thin or very dilute samples

What is happening for thick or concentrated samples?

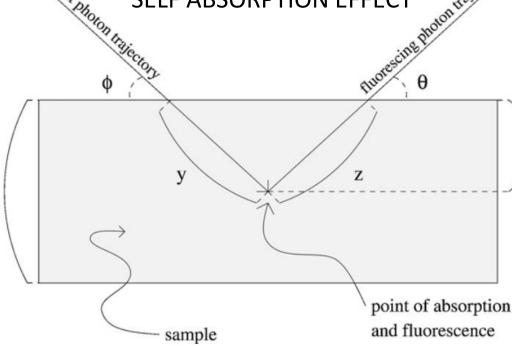




Fluorescence method and the self absorption effect



thick or concentrated samples SELF ABSORPTION EFFECT



The depth into which the incident beam can penetrate changes as fine structure of $\mu(E)$ changes. As the oscillatory part wiggles up, the penetration depth diminishes. As it wiggles down, the depth increases. This serves to attenuate the

 $I_f = I_0 e^{-\mu(E)y} e^{-\mu(E_f)z} \epsilon_a(E) \mu_a(E)$

oscillatory structure.

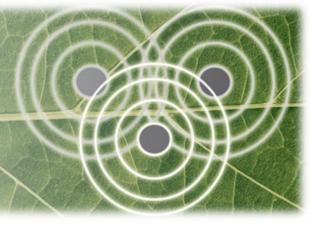
 E_f = energy of the fluorescing photon ϵ_a = fluorescence efficiency per unit solid angle

 μ_a = absorption due to the given core excitation of the absorbing atom





Fluorescence method: the self absorption effect

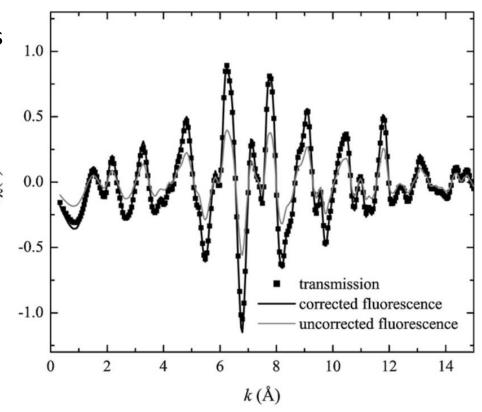


FLUORESCENCE MODE:

thick or concentrated samples SELF ABSORPTION EFFECT

$$\chi = \frac{\chi_{exp}}{1 - \frac{\bar{\mu}}{\alpha} \chi_{exp} - \frac{\bar{\mu}_a}{\alpha}}$$

$$\alpha \equiv \bar{\mu}_T + g\mu_f$$
$$g \equiv \sin \phi / \sin \theta$$







Fluorescence method: detector dead time



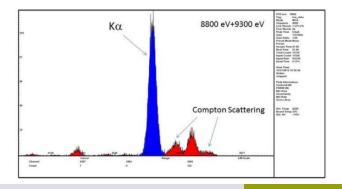
incident x-ray

Sample

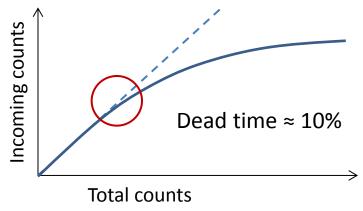
fluorescence +
scattered x-rays



Energy dispersive detector



Dead time: the electronic energy discrimination takes a finite amount of time, which limits the total amount of signal that can be processed. When the count rates are exceeded, the detector is effectively unable to count all the fluorescence for some fraction of the time. The limit of total intensity incident on these detectors can limit the quality of the measured XAFS.

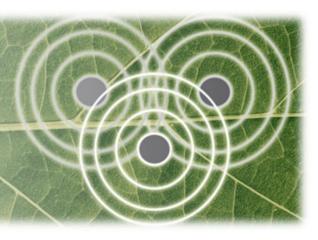




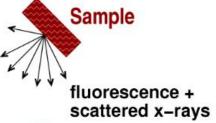
de Separació en Quimica

XANES & EXAFS:

Fluorescence method: detector dead time



incident x-ray

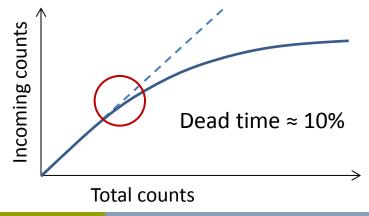




Energy dispersive detector

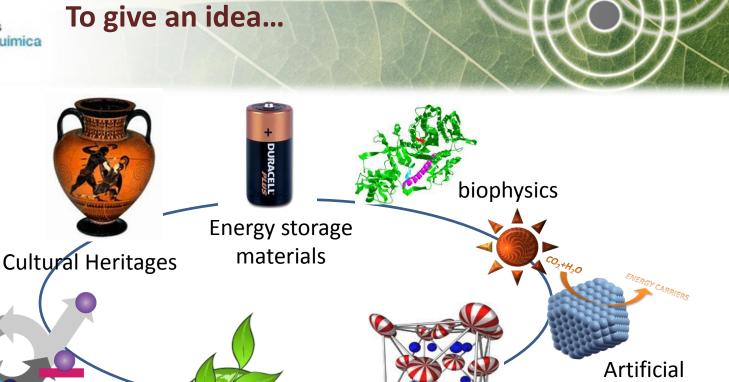
(E discrimination can potentially allow to suppress the scatter peak and other fluorescence lines, collecting only the intensity of the fluorescence lines of interest.)

Dead time: the electronic energy discrimination takes a finite amount of time, which limits the total amount of signal that can be processed. When the count rates are exceeded, the detector is effectively unable to count all the fluorescence for some fraction of the time. The limit of total intensity incident on these detectors can limit the quality of the measured XAFS.





Research fields:



Solid State Physics

Environmental Science

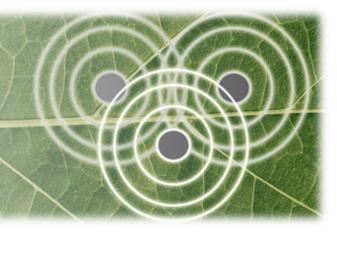
Catalysis

Photosynthesis



Why so many?

To give an idea...





XAS can be applied to any kind of materials:
Crystals, glass, liquids, etc...







SUMMARY





XAS (XANES/EXAFS)

element sensitive local probe that can be applied to any kind of material

COMPLEMENTARY INFORMATION

XANES

- Oxidation state
- Unoccupied electronic states
 - Spin state
 - Local structure
- direct information about bond angles.

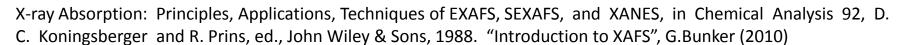
EXAFS

- Bond distances
- Coordination number
- Static and dynamic disorder



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